

Tapered Amplifier

GaAs Semiconductor Laser Diode



Absolute Maximum Ratings

	Symbol	Unit	min	typ	max
Operational Temperature at case	T_C	°C			50
Forward Current	I_F	A			3
Reverse Voltage	V_R	V			0

Stress in excess of the Absolute Maximum Ratings can cause permanent damage to the device. Operation at the Absolute Maximum Rating for extended periods of time can adversely affect the device reliability and may lead to reduced operational life.



Recommended Operation Conditions

	Symbol	Unit	min	typ	max
Operational Temperature at case	T_{case}	°C	0		40
Forward Current	I_F	A			2,5

Characteristics at T_{amb} 25°C

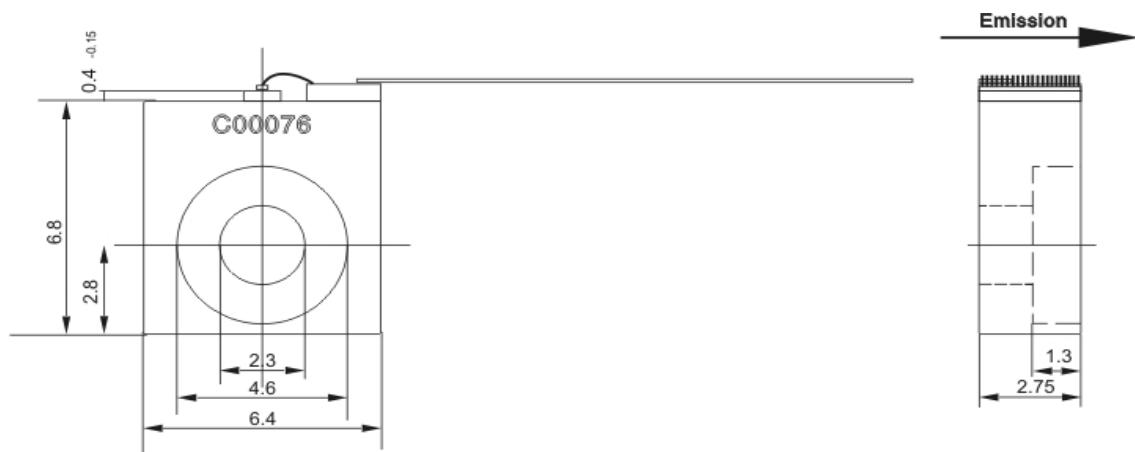
Parameter	Symbol	Unit	min	typ	max	Measurement Condition
Center Wavelength	λ_C	nm	770	780	785	
Gain Width (FWHM)	$\Delta\lambda$	nm	10	20		
Temp. Coeff. of Wavelength	T_{C_λ}	nm / K		0,25		
Output Power	P_{opt}	mW		1000		depending on customer setup
Amplification		dB		13		
Saturation Power	P_{Sat}	mW		50		
Operational Current	I_{Op}	A		2,5		
Cavity Length	l_c	µm		2750		
Input aperture (at rear side)		µm		3		
Output Aperture (at front side)		µm		190		
Divergence parallel (FWHM)	$\Theta_{ }$	°	7	10	13	
Divergence perpendicular ($1/e^2$)	Θ_{\perp}	°		28		
Astigmatism		µm	325	375	425	depending on customer setup
Polarization				TM		

Package Information

	Part No.	
c-Mount 2.75 mm	CMT03	available (see image)
others		on request

Package Dimensions

	CMT03		
Emission plane		mm	7.2 -0.15
C-Mount Thickness		mm	2.75



Package Pinout

	CMT0n	
Cathode (-)		Mounting wire
Anode (+)		Housing

